



N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

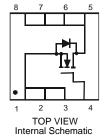
- Case: DFN3030-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Marking Information: See Page 5
- Ordering Information: See Page 5
- Weight: 0.0172 grams (approximate)

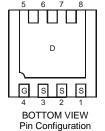


TOP VIEW



BOTTOM VIEW





Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 3)	Steady State	$T_A = 25$ °C $T_A = 85$ °C	ID	7.62 4.83	А
Pulsed Drain Current (Note 4)			I_{DM}	45.9	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3)	P _D	0.99	W
Thermal Resistance, Junction to Ambient @TA = 25°C (Note 3)	$R_{ heta JA}$	126.7	°C/W
Operating and Storage Temperature Range	TJ, T _{STG}	-55 to +150	°C

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 3. Device mounted on FR-4 PCB, with minimum recommended pad layout.
- 4. Repetitive rating, pulse width limited by junction temperature.

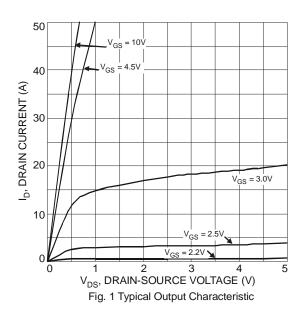


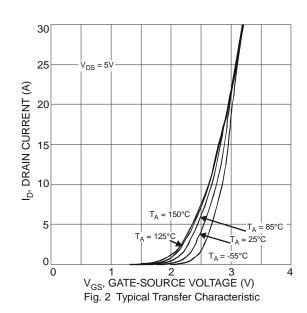
Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 5)							
Drain-Source Breakdown Voltage	BV _{DSS}	30	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T _J = 25°C	I _{DSS}	ı	-	1.0	μΑ	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	1	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 5)							
Gate Threshold Voltage	V _{GS(th)}	1.0	-	2.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance	D	-	10	15	mΩ	$V_{GS} = 10V, I_D = 11.6A$	
Static Dialii-Source Off-Nesistance	R _{DS} (ON)		17	23.5		$V_{GS} = 4.5V, I_D = 10A$	
Forward Transfer Admittance	Y _{fs}	1	8	-	S	$V_{DS} = 10V, I_D = 9A$	
Diode Forward Voltage	V_{SD}	1	0.7	1.0	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 6)							
Input Capacitance	C _{iss}	-	867	-	pF	V 40V V 0V	
Output Capacitance	Coss	ı	85	-	pF	V _{DS} = 10V, V _{GS} = 0V, f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	ı	81	-	pF	1 = 1.0WHZ	
Gate Resistance	R_g	ı	1.39	-	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Qg	-	18.85	-	nC	V _{GS} = 10V, V _{DS} = 15V, I _D = 11.6A	
Gate-Source Charge	Q_{gs}	-	2.59	-	nC		
Gate-Drain Charge	Q_{gd}	-	6.15	-	nC		
Turn-On Delay Time	t _{D(on)}	-	5.46	-	ns	$V_{DD} = 15V, V_{GS} = 10V,$ $R_{L} = 1.3\Omega, R_{G} = 3\Omega,$ $I_{D} = 1A$	
Turn-On Rise Time	t _r	-	14.53	-	ns		
Turn-Off Delay Time	t _{D(off)}	-	18.84	-	ns		
Turn-Off Fall Time	t _f	-	6.01	-	ns		

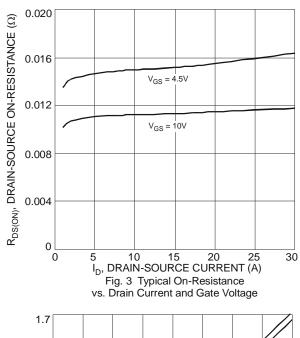
Notes:

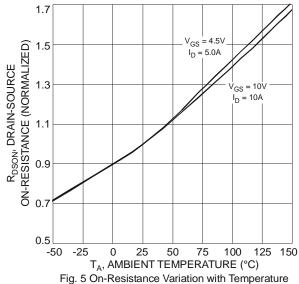
- 5. Short duration pulse test used to minimize self-heating effect.6. Guaranteed by design. Not subject to production testing.

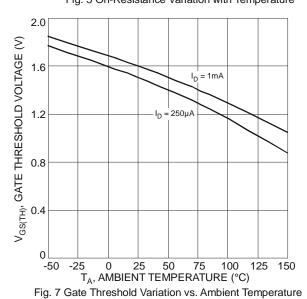


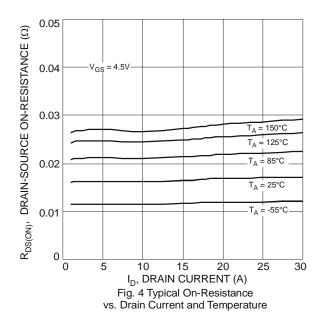


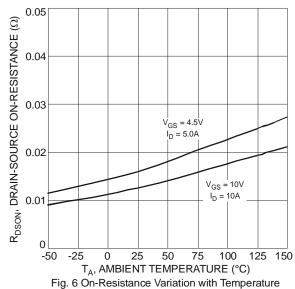












20

16

T_A = 25°C

28

NOS

0

0.2

0.4

0.6

0.8

1.0

1.2

V_{SD}, SOURCE-DRAIN VOLTAGE (V)

Fig. 8 Diode Forward Voltage vs. Current



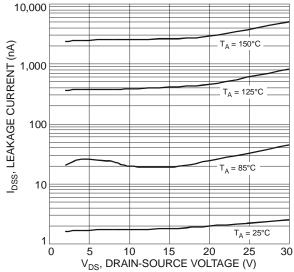


Fig. 9 Typical Leakage Current vs. Drain-Source Voltage

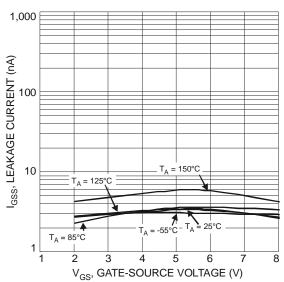
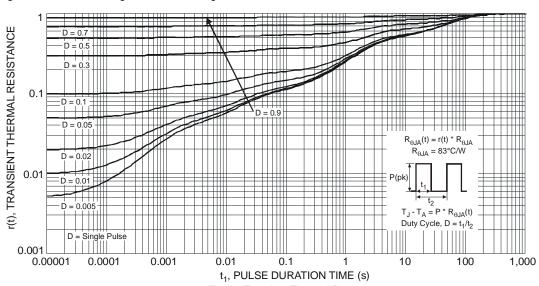


Fig.11 Gate-Source Leakge Current vs Voltage



1,000

I_{GSS}, LEAKAGE CURRENT (nA)

= 125°C

 V_{GS} , GATE-SOURCE VOLTAGE (V)

Fig.10 Gate-Source Leakge Current vs Voltage

= 150°C

Fig. 12 Transient Thermal Response



Ordering Information (Note 7)

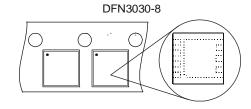
Part Number	Case	Packaging
DMG4468LFG-7	DFN3030-8	3000 / Tape & Reel

Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

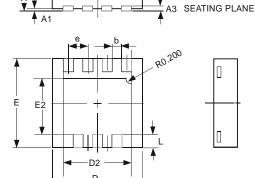
Marking Information



N45 = Product Type Marking Code YYWW = Date Code Marking YY = Last digit of year, ex: 09 for 2009 WW = Week code 01 to 52

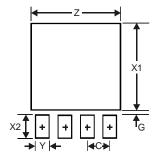


Package Outline Dimensions



DFN3030-8				
Dim	Min	Max	Тур	
Α	0.57	0.63	0.60	
A1	0	0.05	0.02	
A3	_	_	0.15	
b	0.29	0.39	0.34	
D	2.90	3.10	3.00	
D2	2.19	2.39	2.29	
е	_	_	0.65	
Е	2.90	3.10	3.00	
E2	1.64	1.84	1.74	
L	0.30	0.60	0.45	
All Dimensions in mm				

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.59
G	0.11
X1	2.49
X2	0.65
Y	0.39
С	0.65



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